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Supplementary Information

Calculation of the Electronic Parameters of an Al/DNA/p-Si Schottky Barrier Diode Influenced by Alpha Radiation. *Sensors* 2015, *15*, 4810-4822

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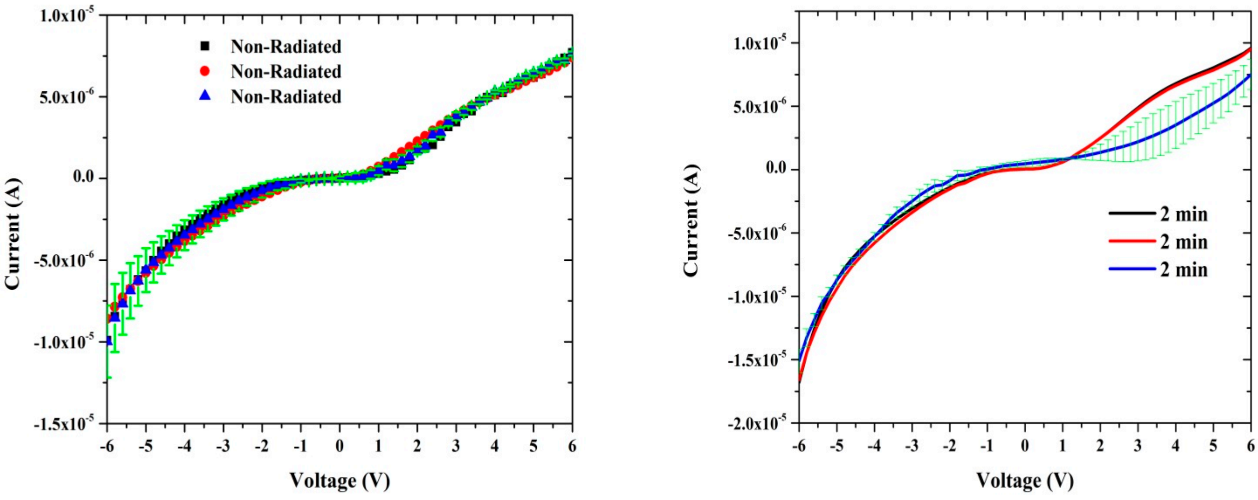
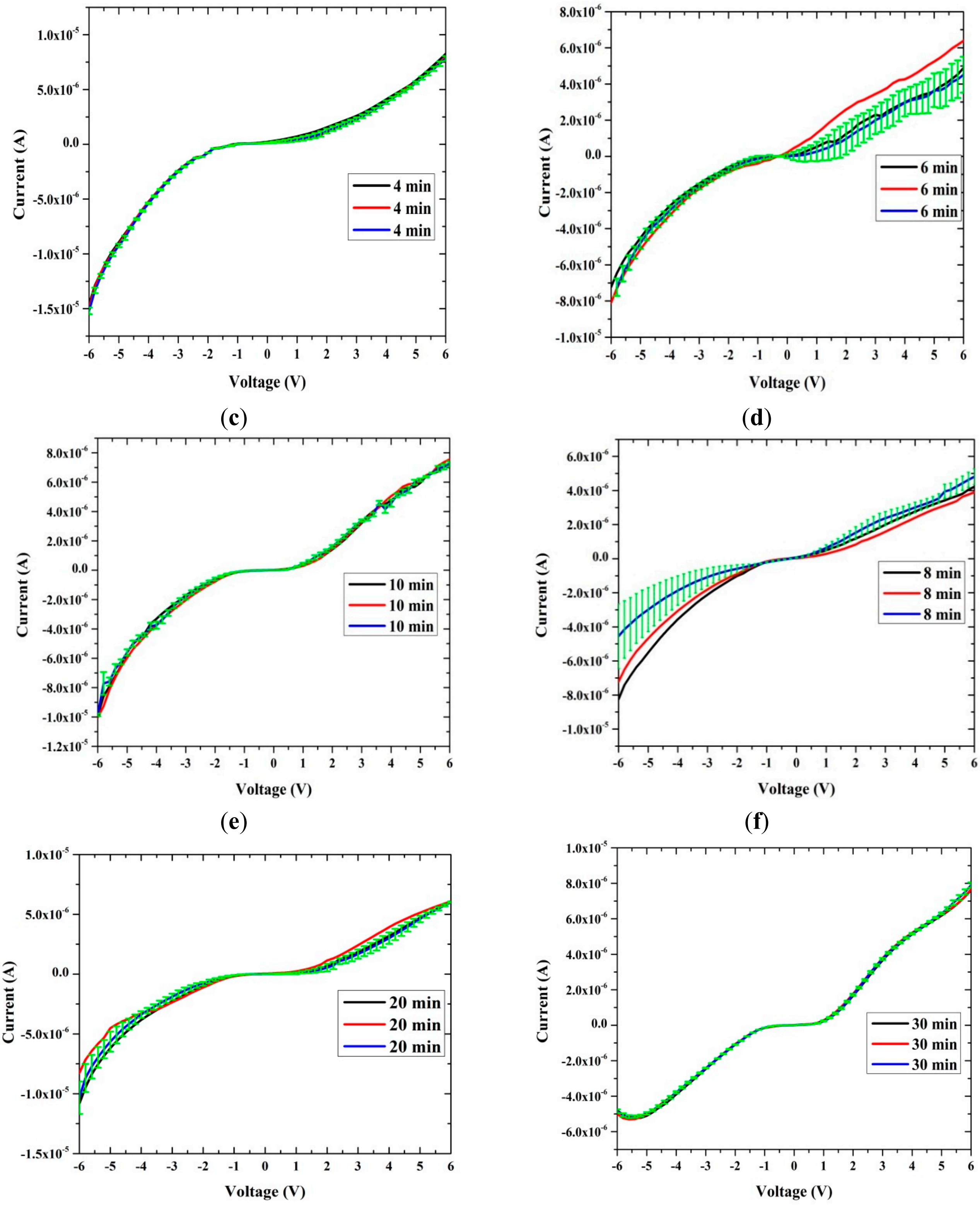


(a) (b)

Figure S1. *Cont.*

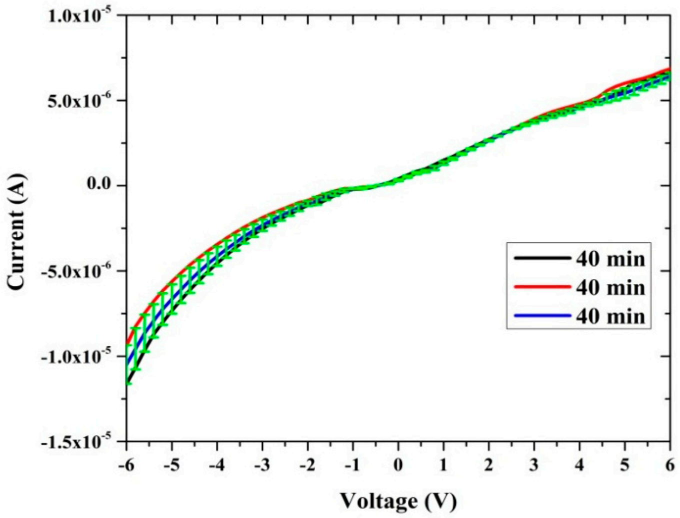


(**c**) (**d**)

(**e**) (**f**)

(**g**) (**h**)

Figure S1. *Cont.*



(**i**)

Figure S1. The I-V graphs demonstrate error bars for (**a**) non-radiated; (**b**) 2 min; (**c**) 4 min; (**d**) 6 min (**e**) 8 min; (**f**) 10 mi; (**g**) 20 min; (**h**) 30 min and (**i**) 40 min.